



ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748-5089

NTE2359 (NPN) & NTE2360 (PNP) Silicon Complementary Transistors Digital w/2 Built-In 47k Bias Resistors

Features:

- Built-In Bias Resistor ($R_1 = 47\text{k}\Omega$, $R_2 = 47\text{k}\Omega$)
- Small-Sized Package (TO92 type)

Applications:

- Switching Circuit
- Inverter
- Interface Circuit
- Driver

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector to Base Voltage, V_{CBO}	50V
Collector to Emitter Voltage, V_{CEO}	50V
Emitter to Base Voltage, V_{EBO}	10V
Collector Current, I_C	
Continuous	100mA
Peak	200mA
Collector Dissipation, P_C	300mW
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{Stg}	-55° to +160°C

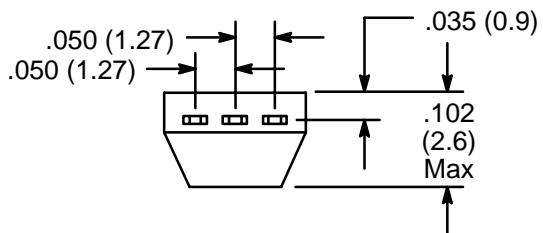
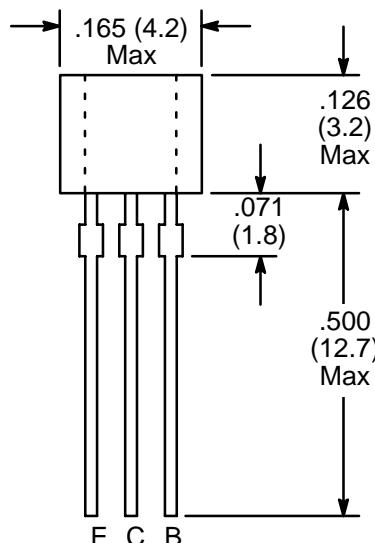
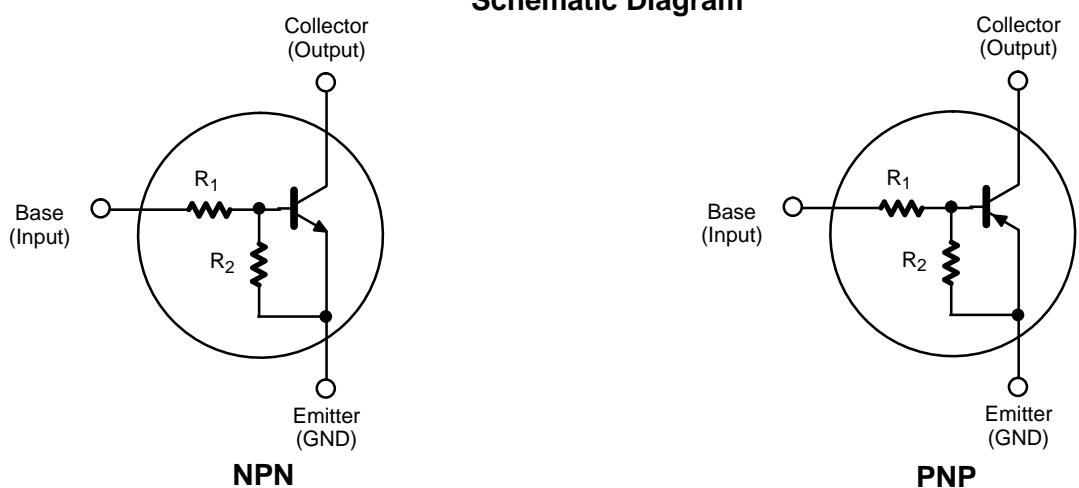
Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 40\text{V}$, $I_E = 0$	-	-	0.1	μA
	I_{CEO}	$V_{CE} = 40\text{V}$, $I_B = 0$	-	-	0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$	30	53	80	μA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 5\text{mA}$	50	-	-	
Gain Band-width Product NTE2359	f_T	$V_{CE} = 10\text{V}$, $I_C = 5\text{mA}$	-	250	-	MHz
NTE2360			-	200	-	MHz
Output Capacitance NTE2359	C_{ob}	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$	-	3.7	-	pF
NTE2360			-	5.5	-	pF

Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 5\text{mA}, I_B = 0.25\text{mA}$	-	0.1	0.3	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\mu\text{A}, R_{BE} = \infty$	50	-	-	V
Input OFF Voltage	$V_{I(\text{off})}$	$V_{CE} = 5\text{V}, I_C = 100\mu\text{A}$	0.8	1.1	1.5	V
Input ON Voltage	$V_{I(\text{on})}$	$V_{CE} = 200\text{mV}, I_C = 5\text{mA}$	1.0	2.5	5.0	V
Input Resistance	R_1		32	47	62	k Ω
Input Resistance Ratio	R_1/R_2		0.9	1.0	1.1	

Schematic Diagram



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